### SILICON (Si) POWER MOSFET A CEZC3P07A



CET MOS

# CEZC3P07A

# -30V ▲ 8mΩ ▲ -37A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type PN-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK3x3 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

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RoHS

REACH

## **MAXIMUM RATINGS**

Parameter (T <sub>c</sub> = 25°C, unless otherwise noted)	Characteristics			
Drain-Source Voltage	V <sub>DS</sub>	-30V		
Gate-Source Voltage	V <sub>GS</sub>	±20V		
Continuous Drain Current at R <sub>TH_JC</sub>	I <sub>D</sub>	-37A at T <sub>c</sub> = 25°C	-23A at T <sub>c</sub> = 100°C	
Continuous Drain Current at R <sub>TH_JA</sub>	Ι <sub>D</sub>	-11A at T <sub>A</sub> = 25°C	-7A at T <sub>A</sub> = 100°C	
Pulsed Drain Current at R <sub>TH_JC</sub> Note 1	I <sub>DM</sub>	-148A at T <sub>c</sub> = 25°C		
Pulsed Drain Current at R <sub>TH_JA</sub> Note 1	I <sub>DM</sub>	-44A at T <sub>A</sub> = 25°C		
Maximum Power Dissipation at R <sub>TH_JC</sub>	PD	25W at $T_c = 25^{\circ}C$		
Maximum Power Dissipation at R <sub>TH_JA</sub>	PD	2.5W at T <sub>A</sub> = 25°C		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C		

# **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case Note 2	R <sub>TH_JC</sub>	5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	50°C/W

# **APPLICATIONS**

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			4	Ŷ

# **PIN DESCRIPTION**

Circuit Diagram	Outline • Bottom View	Pin No.	Description
D (5) G (4) S (1,2,3)		1 2 3 4 5	Source Source Gate Drain

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# **ELECTRICAL CHARACTERISTICS** A T<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV <sub>DSS</sub>	-30			V
Zero Gate Voltage Drain Current	$V_{DS}$ = -30V, $V_{GS}$ = 0V	I <sub>DSS</sub>			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	V <sub>GS(th)</sub>	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$ , $I_{D} = -10A$	R <sub>DS(ON)</sub>		8	10	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V, I_{D} = -5A$	R <sub>DS(ON)</sub>		11.5	15	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		2020		pF
Output Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>OSS</sub>		390		рF
Reverse Transfer Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		170		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = -10A, $R_{\text{G}(\text{ext})}$ = 6 $\Omega$	t <sub>D(ON)</sub>		18		ns
Turn-On Rise Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = -10A, $R_{G(ext)}$ = $6\Omega$	t <sub>R</sub>		8		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = -10A, $R_{G(ext)}$ = $6\Omega$	$t_{D(OFF)}$		108		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = -10A, $R_{G(ext)}$ = $6\Omega$	t <sub>F</sub>		31		ns
Total Gate Charge	$V_{DS} = -15V, V_{GS} = -5V, I_D = -10A$	Q <sub>G</sub>		21		nC
Gate Source Charge	$V_{DS} = -15V, V_{GS} = -5V, I_D = -10A$	Q <sub>GS</sub>		7		nC
Gate Drain Charge	$V_{DS}$ = -15V, $V_{GS}$ = -5V, $I_{D}$ = -10A	$Q_{\text{GD}}$		10		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		I <sub>S</sub>			-2.5	А
Drain-Source Diode Forward Voltage <sup>Note 3</sup>	$V_{GS} = 0V, I_{S} = -1A$	$V_{\text{SD}}$			-1	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec.

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4: Guaranteed by design, not subject to production testing.

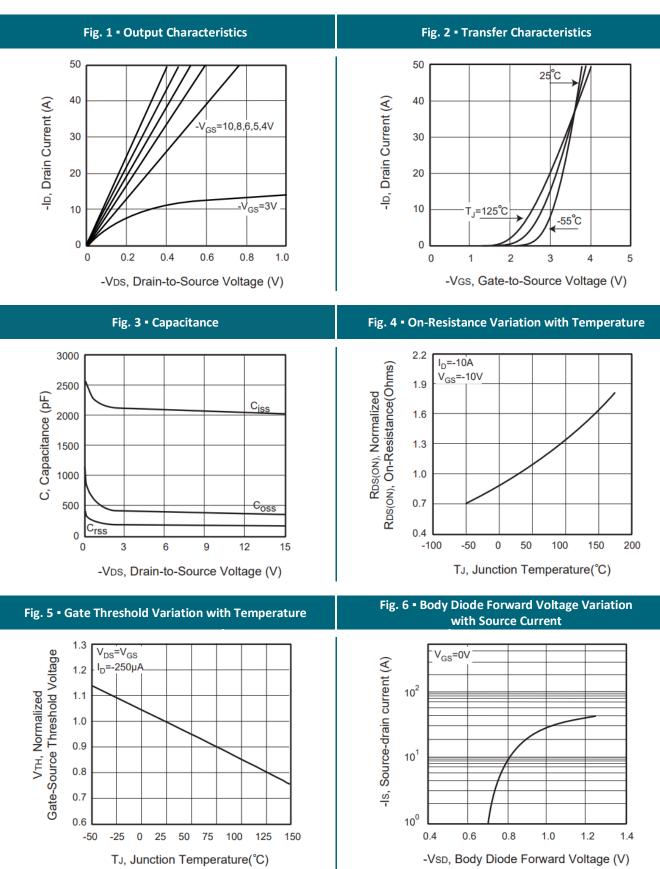


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# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



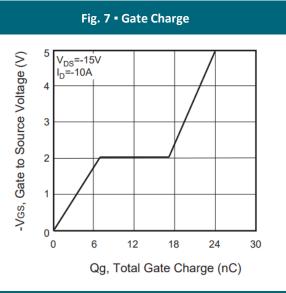
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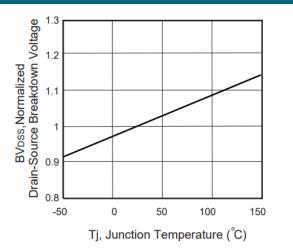


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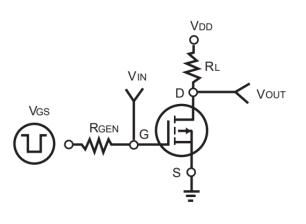
# **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



#### Fig. 9 - Breakdown Voltage Variation vs. Temperature







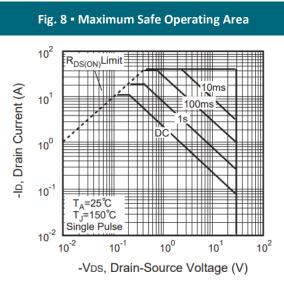
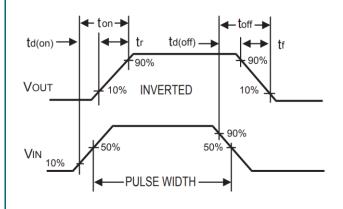


Fig. 11 • Switching Waveforms



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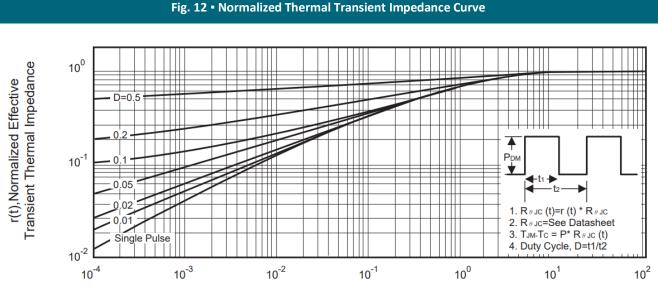
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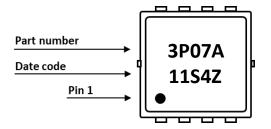
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# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



Square Wave Pulse Duration (sec)

# **PART MARKING**



# DATE CODE

Example: 11S4Z



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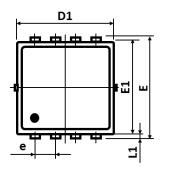
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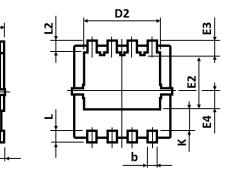
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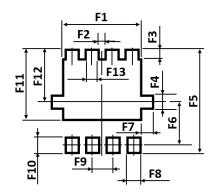


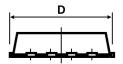
# PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT

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Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.700	-	0.850	E2	1.540	-	1.940
b	0.200	-	0.400	E3	0.280	-	0.650
с	0.100	-	0.250	E4	0.370	-	0.770
D	3.000	-	3.450	е		0.650 (BSC)	
D1	3.000	-	3.250	К	0.500	-	0.890
D2	2.290	-	2.650	L	0.300	-	0.500
E	3.150	-	3.450	L1	0.060	-	0.200
E1	2.900	-	3.200	L2	0.270	-	0.570

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	2.500	-	F8	-	0.350	-
F2	-	0.300	-	F9	-	0.650	-
F3	-	0.400	-	F10	-	0.500	-
F4	-	0.430	-	F11	-	2.280	-
F5	-	3.350	-	F12	-	1.700	-
F6	-	1.400	-	F13	-	0.350	-
F7	_	0.420	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

# **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEZC3P07A	PPAK 3x3	Reel	5,000pcs	10,000pcs	80,000pcs

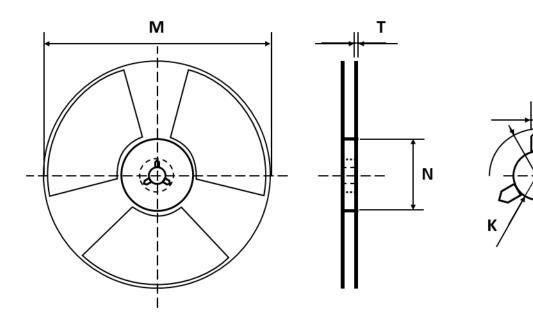


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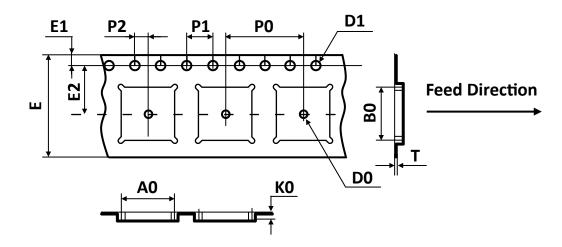


# **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

# TAPE DIMENSIONS All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
РРАК ЗхЗ	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30 -0.10	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02

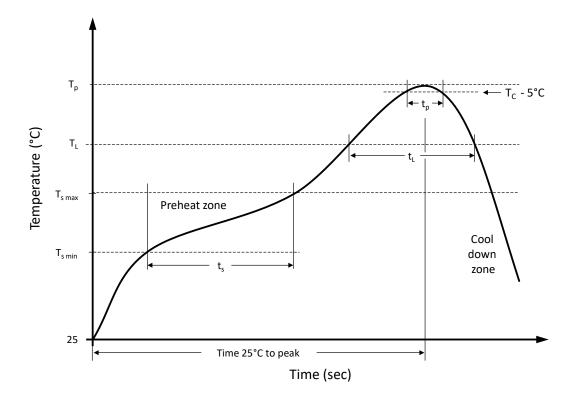


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# **RECOMMENDED REFLOW SOLDERING PROFILE**



## **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



# **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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